

Index

A

- Acceptance function, 401
- Acceptance range increase requirements, 477, 478
- Aluminum nitride (AlN), 114
- Aluminum oxide (Al₂O₃), 108
- Analyzer, 188
- Angle-lapping and stain method (ASTM), 217, 218
- Angstroms accuracy, 188
- Anisotropic wet etching
 - aqueous alkaline solutions, 134
 - crystallographic orientation alignment, 137
 - dimensional variations, 137
 - dopant etch stops, 136
 - EDP, 135
 - etch rate, 135
 - fabrication methods, 136
 - labor-intensive operation, 136
 - lateral etch variation, 137
 - mask, 133
 - material etch stops, 137
 - SEM images, 134
 - silicon nitride, 135
 - silicon substrate, 132
 - single-crystal silicon, 131
 - single-crystal substrate, 133
- Argon fluoride (ArF), 79
- Aspect ratio dependent etching (ARDE), 91
- Atmospheric chemical vapor deposition (ACVD), 54
 - carrier gases, 56
 - cold wall reactor, 56
 - commercial-grade systems, 56
 - CVD process, 55
 - deposition rates, 56
 - equipment setup, 55
- Atomic force microscope (AFM)
 - Casimir forces, 210
 - deflection, 209
 - Hooke's law, 209
 - imaging modes, 209
 - material properties, 208
 - mechanical forces, 209
 - MEMS fabrication techniques, 208
 - noncontact mode, 210
 - scanning probe methods, 210
 - sharp-tipped probes, 208
 - surface topology resolution, 210
 - van der Waals forces act, 210
- Atomic layer chemical vapor deposition (ALCVD), 54
- Atomic layer deposition (ALD), 54, 60, 107, 108, 110, 189
 - gas-phase reactions, 62
 - precursor monolayer deposition, 60
 - precursor reactions, 62
 - process chamber, 61
 - process gases, 60, 61
 - process reactor design, 61
- Auger electron spectrometry (AES), 213, 214

B

- Batch fabrication techniques
 - die-saw machine, 33
 - LLPCVD, 33
 - manufacturing processes, 32
 - production method, 32
 - silicon wafers, 33

- Batch fabrication techniques (*cont.*)
 - substrates, 33
 - Bell-shaped curve, 359
 - Berkovich tip, 243
 - Best-case dimensional variations, 93
 - Best practices, mask layout design
 - asymmetric design layout, 483
 - common centroid design techniques, 482
 - components, 478
 - desired resistor network configuration, 480
 - dummy devices, 483, 484
 - effect of feature orientation, 479
 - geometrical shapes, 479
 - inter-digitation, 480, 481
 - large and small features, 485
 - MEMS resonator device, 481
 - microfabrication, 479
 - parallel conduction paths, 485
 - parameter values, 479
 - process gas diffusion effects, 483
 - switched capacitor circuit, 478
 - Bias variation, 316
 - Boundary element method (BEM), 453
 - Bulk micromachining, 129
 - anisotropic wet etchants, 131–137
 - isotropic wet etching, 130, 131
 - wet chemical etchants, 129
- C**
- Calibration, 177
 - Capacitance-voltage (CV) measurements, 243
 - Capacitive effect, 15
 - dielectric material, 14
 - inertial sensor, 14
 - transduction method, 13
 - Cassette-to-cassette systems, 78
 - Ceramics, 113
 - CFD software, 456
 - Charge-coupled device (CCD), 201
 - Chemical solution deposition (CSD), 114, 115
 - Chemical vapor deposition (CVD)
 - ACVD, 55, 56
 - ALD, 60–62
 - chemical reactions, 52
 - crystallographic order, 53
 - fluxes, 53
 - growth rate, thin-film, 53
 - in situ doped CVD, 52
 - LPCVD, 56–58
 - mass transfer controlled region, 53
 - material types, 55
 - PECVD, 58–60
 - PSG, 54
 - SiN, 54
 - single-crystal silicon, 54
 - stages, 52
 - steady-state conditions, 53
 - stoichiometric form, 54
 - sub-categories, 54
 - surface reaction controlled, 53
 - TEOS, 54
 - thin-film material layers, 52
 - zero stress state, 54
 - Chemical-mechanical polishing (CMP), 84, 85, 292
 - Chi-squared distribution, 351
 - Chi-squared testing, 341
 - Clamped-clamped beam configuration, 237, 238
 - CMOS imaging camera, 201
 - Coherence scanning interferometry (CSI), 199
 - Compound microscope, 175
 - Computation fluid dynamics (CFD) software, 456
 - Computer numerical control (CNC) machine tools, 324
 - Confocal microscopy, 179, 180
 - Contact mode imaging, 209
 - Contact photolithography, 121
 - Copper (Cu), 117
 - Critical dimension (CD), 181
 - Czochralski crystal growing method, 39, 41
- D**
- Dark-field microscopy, 176
 - Deal and Grove model, 49
 - Deep reactive ion etching (DRIE), 129, 142, 143, 183
 - Bosch™ process, 139
 - dimensional variations, 140
 - DSE, 140
 - micromachining method, 139
 - photoresist, 140
 - silicon, 139
 - single-crystal silicon substrates, 138
 - Deep Silicon Etch (DSE), 140
 - Deep, high-aspect ratio etching (DRIE), 129
 - Deep-ultraviolet (deep-UV), 77
 - Deep-ultraviolet (DUV), 325
 - Department of Defense (DoD), 2
 - Design centering, 468, 506
 - acceptance range, 473
 - bias variations, 470, 473
 - dynamic viscosity, 469

- flow resistance, 469, 471
 - manufacturing yield, 472
 - microchannel device, 469
 - microchannel length, 471
 - Monte Carlo analysis, 469
 - nominal values, 469
 - photolithography and etching steps, 472
 - probability distribution functions, 469, 470
- Design for manufacturability (DfM), 448
 - LPCVD/PECVD processes, 460
 - microsystems partitioning, 462–463
 - parameter variations, 458
 - photolithographic and etching processes, 459
 - process sequence, 460–461
 - recommendations, 466–467
 - source and magnitude, 458
 - statistical data, 458
- Design levels
 - CFD software, 456
 - electrical resistor, 457
 - Hagen-Poiseuille relationship, 457
 - lateral dimensions, 454
 - microchannel device, 454, 455
 - Navier-Stokes equations, 454, 455
 - physical equations, 456
 - thin-film material masking layer, 454
 - volumetric flow rate, 457
- Design of experiments (DOE), 229, 280
- Design rule checking (DRC), 303, 452
- Device dimensional parameter variations, 321
- Device parameter variations, 2, 447
 - bias and random variation, combination, 359, 360
 - bias variation, 316
 - dimensional parameters, 313
 - generalizations, import
 - Correlation, 373–375
 - microfabricated devices, 373
 - probability distribution function, 372, 374, 375
 - manufacturing method
 - actual/resultant value, 314
 - desired value, 314
 - relative variation, 315
 - repeatability, 315
 - reproducibility, 315
 - stability, 315
 - manufacturing variations, measurement, 315
 - MEMS design, 467
 - methods, 468
 - micro-and nano-fabrication, 506
 - microsystems manufacturing
 - accuracy, 319, 387
 - precision, 319, 320, 387
 - resolution, 319
 - tolerance, 321
 - optical radiation, 297
 - output behavior
 - device parameters, 363
 - dynamic viscosity, 366
 - laminar flow characteristics, 363
 - manufacturing function, 368
 - mean value, 362
 - measurements, 361
 - microchannel device, 364, 365, 367
 - microchannel dimensions, 366
 - microchannel flow resistance, 369–371
 - microchannel parameters, 368
 - microchannel radius and length, 366
 - microchannel width, 365
 - physical equations, 361
 - tolerance interval, 367
 - photolithographic constraints, 295
 - photolithographic pattern, 296
 - photoresist, 297
 - Physics and Random variation, impact
 - anisotropic etching, 356
 - DRIE technique, 356
 - example, 355
 - Hagen-Poiseuille equation, 355
 - microchannel, 355, 356
 - microfluidic flow channel, 358
 - Poisson's ratio, 359
 - power of radius, 358
 - substrate, 356
 - projection optical system, 295
 - random variations, 317, 318
 - standard deviations, 375
 - statistical analysis
 - confidence interval, manufacturing large sample, 345, 346
 - confidence interval, small samples, 347
 - hypergeometric distribution, example, 354
 - hypothesis testing, 348
 - Poisson distribution, example, 354
 - thin-film deposition, 297
 - topography, 295
 - variation analysis, 370, 372
- Device size scaling, 468
 - disadvantage, 476
 - issue, 476
 - Monte Carlos analysis, 476
 - photolithography, 475

- Device size scaling (*cont.*)
 - probability distribution function, 477
 - thermal oxidation, 477
 - wet etched microchannel parameters, 476
 - Device under test (DUT), 304
 - Diamond-like carbon (DLC), 106
 - Differential interference contrast (DIC)/
Nomarski microscopy, 176
 - Diffusion furnace, 71
 - Digital Light Processor (DLP[®]) technology, 463
 - CMOS microcircuit, 292
 - CMP, 292
 - disruptive technology, 291
 - DMD, 291–293
 - elements, 294
 - integrated microelectronics, 291
 - sacrificial polymer layer, 293
 - Digital Micromirror Device (DMD), 291
 - Dimensional parameter variations
 - CNC tools, 324
 - DUV, 325
 - EUV, 325
 - fabrication process, 324, 325
 - macro-dimensional scale, 323
 - microfabrication process, 323–325
 - microscale beam, 322
 - RIE, 325
 - Diode devices, 21, 22
 - Direct-write laser photolithography, 122
 - Discrete probability distributions/binominal
distribution
 - hypergeometric, 344
 - manufacturing yield analysis, 342
 - Pascal distribution, 343
 - Poisson, 344, 345
 - properties, 342
 - Dry etching, 108
- E**
- Electrical material properties test methods, 223
 - junction depth measurements, 217–218
 - spreading sheet resistance, 218–221
 - Electrical properties electrical properties, 254
 - Electrical rule checking (ERC), 452
 - Electrical test structures
 - CV measurements, 243, 244, 246
 - high- and low-frequency voltages, 244
 - metal layer, 250
 - metal lines, 244
 - MOS, 244
 - reciprocity theorem, 248
 - ring oscillator, 250
 - testing pads, 247
 - types, 243
 - van der Pauw test structure, 248
 - Electrochemical deposition methods, 267, 268
 - anode, 119
 - cathode, 118
 - dimensional variations, 120
 - electroless plating, 119
 - electroplating, 118, 119
 - wetting agents, 119
 - Electrochemical fabrication (EFAB), 155
 - Electro-discharge micromachining, 153
 - Electron-beam (e-beam) lithography, 124, 125
 - Electron-beam physical vapor deposition
(EBPVD), 63
 - Electron spectroscopy for chemical analysis
(ESCA), 214
 - Electronic-grade silicon (EGS), 39
 - Electrostatic actuation, 23, 24
 - Ellipsometry, 187, 188
 - Energy-dispersive X-ray spectroscopy (EDS),
182, 210, 212
 - Etching
 - anisotropy, 90
 - ARDE, 91
 - dimensional control, 91
 - electromagnetic field oscillates, 89
 - features, 92
 - individual steps, 87, 88
 - lag, 91
 - lateral etch, 90
 - loading effect, 90
 - mask selectivity, 90
 - parameters, 89
 - pattern, 91
 - plasma discharge, 87
 - process flow, 86
 - processes, 86
 - RIE, 86–88
 - robotic automation, 87
 - steady-state condition, 87
 - Evaporative physical vapor deposition, 263,
265
 - Extreme ultraviolet (EUV), 325
- F**
- Fabrication metrology
 - automated scanning electron microscope,
183–184
 - confocal microscopy, 179, 180
 - ellipsometry, 187, 188

equipment and methods, 222
 fluorescence microscope, 177, 178
 interferometry, 185, 186
 optical microscopy, 174–177
 SEM, 180
 stereomicroscope, 179, 180
 stylus profilometer, 189–191
 Finite element method (FEM), 453, 456
 Flash evaporation, 116
 Fluorescence microscope, 177, 178
 Focused ion beam (FIB), 154, 155
 conductive and nonconductive materials, 204
 features, 203
 gallium ion source, 203
 nanometer dimensional-scale machining, 204
 photolithographic mask repair, 205
 SEM, 204, 205
 SIMS, 205
 sputtered ions/secondary electrons, 203
 surgical cross-sectioning and imaging, 204
 tool, 203
 x-ray spectroscopy, 205
 Fourier-transform infrared spectroscopy (FTIR), 216
 Four-point probe
 contour-mapping profile, 193
 dopant impurities, 191
 electrical material properties, 191
 metals layers, 191
 resistivity value, 192
 sheet resistance, 191, 192
 thin-film metal layers, 192
 Fringe rings, 202
 Front-to-back contact photolithography, 121
 MEMS device fabrication, 121
 pressure sensor, 121
 Functional and parametric testing, 305
 Functional yield
 defects, examples, 394, 395
 measuring tools
 confocal microscopy, 399
 conventional SEMs, 399
 MEMS microsystems devices, 399
 models, microsystem, 394
 models, point defects
 cluster parameter, 397, 398
 densities, 398, 399
 gamma function, 397
 limitation, 396
 MEMS microsystems, 395
 non-uniform defects, 396
 Functional yield testing, 305, 393

G

Gallium arsenide (GaAs), 39
 Gallium nitride (GaN), 39
 Gas-phase isotropic chemical etchants
 XeF₂, 137, 138
 Gauge factor (GF), 12
 Germanium (Ge), 104
 Graphic Database System II (GDSII), 452
 Grayscale photolithography, 122, 123

H

Hagen-Poiseuille equation, 355
 Hagen-Poiseuille relationship, 457
 High-electron mobility transistors (HEMTs), 39
 High-energy ion scattering (HEIS), 215
 Highly specialized metrology method
 AES, 213, 214
 equipment and methods, 223
 FTIR, 216
 LIMS, 215
 NAA, 215, 216
 Raman spectroscopy, 216
 RBS, 215
 SIMS, 213
 STEM, 213
 TEM, 212
 XPS, 214
 x-ray diffraction, 213
 XRF, 214, 215
 Hot embossing, 152
 Hydrofluoric acid (HF), 261, 289
 Hypergeometric distribution, 344
 Hypothesis testing, 348
 chi-squared distribution, 351
 estimation population mean, sample size, 353
 expected frequencies, calculation, 352
 left-tailed test, 348, 350
 right -tailed test, 348, 349
 statistical parameters, 348, 350, 351
 two-tailed test, 348

I

Image reversal photoresists, 127
 Impurity doping
 attributes, 68
 ion implantation, 68
 methods, 68
 p–n junction, 67
 semiconductor, 68
 thermal diffusion, 68–71
 Indium phosphide (InP), 39

- Inductively coupled plasma (ICP), 142, 143
- Infrared inspection method, 202
- Integrated circuit (IC) processing steps, 9
 - best-case dimensional variations, 93, 94
 - categories, 45
 - clean and strip, 92, 93
 - CVD (*see* Chemical vapor deposition (CVD))
 - dimensional parameter variations, 47
 - dopants (*see* Impurity doping)
 - etching (*see* Etching)
 - group types, 46
 - metrology technologies, 45
 - photolithography (*see* Photolithography)
 - planarization, 83–85
 - process sequence, 45
 - RTA (*see* Rapid Thermal Anneal (RTA))
 - sequential manner, 45
 - thin-film deposition technologies (*see* Thin-film deposition technologies)
 - wafer-level tests, 46
- Integrated MEMS process, 283
- Inter-digitation, 480, 481
- Interferometry, 185, 186
- Internet of Things (IoT), 4
- Ion implantation
 - advantages, 75
 - attribute, 71
 - diffusion processes, 75
 - dopant profiles, 72
 - dosage, 74
 - equipment, 74
 - Gaussian distribution, 74
 - orthogonal distance, 72
 - penetration profile, 72
 - semiconductor, 73
 - sufficient energy, 72
 - wafer-to-wafer variation, 75
- Iterative method, 353

- J**
- Junction depth, 70

- L**
- Large-scale integrated circuits (LSI), 1
- Large topography, 125, 126
- Laser ionization mass spectroscopy (LIMS), 215
- Laser micromachining, 117, 153, 154
- Lateral etch, 140
- Layout versus schematic (LVS), 452

- Lead zirconate titanate (PZT), 114
- Lift-off patterning, 126, 127
- Line-edge roughness (LER), 184
- Line-width roughness (LWR), 184
- Linnik interferometry, 199
- Lithographie, Galvanoformung, Abformung (LIGA), 124, 150–152
- Loading, 460
- Lorentz equation, 29
- Lower control limit (LCL), 425
- Low-pressure chemical vapor deposition (LPCVD), 30, 33, 54, 56–58, 284
 - silicon dioxide (SiO₂), 255, 257
 - silicon nitride (SiN), 257–260
- Low-temperature oxide (LTO), 110

- M**
- Macroscale temperature sensors, 21
- Magnetic effects, 18, 19
- Magnetic materials, 117, 118
- Magnetics, 28, 30
- Magnetron-type sputtering systems, 67
- Manufacturing function, 402, 445
- Material properties
 - carrier types, 228
 - design and development, 229
 - DOE, 229
 - impact, 229
 - mechanical, 228
 - mechanical test structures (*see* Test structures)
 - MEMS process sequences, 227
 - residual stress, 232, 233
 - single-layer, 228
 - SPC methods, 228
 - thin-film material layers, 228
 - values, 229
 - Young's modulus, 230–232
- Materials deposition processing
 - electrochemical deposition, 118–120
- MEMS
 - design, 43, 448
 - implementation, 43
 - materials deposition processing (*see* Thin-film semiconductors)
 - substrate materials, 100, 101
- MEMS design rules, 301–303
- MEMS device
 - activities, 448
 - concepts, 448
 - design activity, 453
 - design for manufacturability, 448

- development
 - advanced modeling software, 463
 - IC industry design, 464
 - iterative process, 465
 - mask design, 464
 - open-loop manufacturing process, 465
 - parameter variations, 465
 - process sequence, 464
 - satisfactory design, 464
 - statistical dimensional data, 465
 - system-level model, 464
 - test structures, 464
- device parameter variations, 448
- DfM (*see* Design for Manufacturability (DfM))
- FEM methods, 453
- GDSII, 452
- geometric variations, 461
- hierarchical layers, 451, 452
- levels (*see* Design levels)
- lump-element components, 453
- modeling, 451
- modeling tools, 454
- numerical techniques, 453
- photolithographic patterning, 452
- physical describing equations, 448
- process sequence, 451
- rule checking, 452
- software tools, 454
- TCAD, 452
- verification capabilities, 452
- MEMS devices
 - design methods, 485, 486
- MEMS microactuators
 - electrostatic, 23, 24
 - piezoelectric transducers, 24–26
 - SMAs, 27, 28, 30
 - thermal, 26, 27
- MEMS microsensors
 - capacitive effect, 13, 15
 - diode, 21, 22
 - magnetic, 18, 19
 - photoconduction effect, 19, 20
 - physical transduction principles, 10
 - piezoelectricity, 15, 16
 - piezoresistive, 12, 13
 - resistor, 10–12
 - thermoelectric effect, 20–22
 - tunneling, 16, 17
- MEMS microsystems
 - attributes, 4, 6
 - criterion, 3
 - definition, 2
 - device parameter, 7
 - fabrication techniques, 3
 - metrology techniques, 6
 - micro-and nano-fabrication, 2
 - microactuators, 3
 - microsensors, 3
 - Moore's Law, 4
 - process sequence, 6
 - processing steps, 6
 - smart systems, 4
 - SPC, 7
 - technologies, 4
- MEMS process technologies, 282
- Metal organic chemical vapor deposition (MOCVD), 54
- Metal oxide semiconductor (MOS) devices, 54, 244
- Metals
 - MEMS fabrication, 106
 - noble, 107
 - qualitative properties, 107
 - RIE, 108
- Metrology
 - fabrication (*see* Fabrication methodology)
 - manufacturing, 173
 - MEMS microsystems, 173
 - tools and methods, 173
- Microactuators, 3
- Micro-electromechanical systems (MEMS), 2
- Microfabrication proces, 323
- Microminiaturized devices, 43
- Microresonators, 3
- Microsensors, 3
- Microsystem manufacturing yield
 - economic importance, 391
 - manufacturing process, 390
 - production processes, 389
 - resultant variations, 390
 - substrates, 389, 390
- Microsystems, 144
 - micro-and nano-fabrication, 30
- Microsystems device design
 - acceptable level of performance, 447
 - fabrication steps, 449
 - functionalities, 447
 - level, 449
 - manufacturing process, 447
 - processing steps, 449
 - production level, 447
 - technology levels, 449
- Microsystems manufacturing yield
 - definition, 390
 - fabrication process, 390

- Microsystems manufacturing yield (*cont.*)
 - substrate manufacturing, 391, 392
- Microsystems packaging, 307, 309, 310
- Microsystems testing
 - calibration, 307
 - detecting failures, 304
 - device trimming, 306, 307
 - DUT, 304
 - fabricated devices function, 304
 - functional yield, 305
 - input signals, 304
 - MEMS sensor, 306
 - parametric, 305
 - procedure, 305
- Mirau interferometry, 199
- Monte Carlo analysis technique, 382, 503, 506
 - acceptance region boundaries, 492
 - analyses, 497
 - design centering, 494
 - centers of gravity algorithm, 493, 494
 - variation region, 495
 - error function, 495
 - Gaussian distribution, 495
 - manufacturing yield, 493
 - method, 498
 - microsystems devices, 491
 - parameter space, 492
 - pass points, 493
 - positive correlation, 496
 - probability density function, 496
 - probability distribution function, 495
 - pseudorandom points, 496, 497
 - regionalization/simplicial approximation, 492
 - systematic methods, 492
 - variation region, 498
- Multidimensional spaces
 - acceptance region, 487
 - design parameters, 486, 487
 - fabrication methods, 489
 - flow resistance, 490
 - nominal parameter values, 489
 - parameter variation, 487
 - performance functions, 491
 - probability distribution function, 489, 490
 - regions of variation and acceptance, 488
- Multivariate parameter space, 502

- N**
- Nano-electromechanical systems (NEMS), 2
- Navier-Stokes equations, 454
- Neutral-Loop Discharge (NLD), 142

- Neutron activation analysis (NAA), 215, 216
- Newton rings, 202
- Noncontact mode, 210
- Noncontact surface profilometers
 - CSI mode, 200
 - frames, 199
 - mechanical translation, 199
 - metrology tools, 198
 - monochromatic light source, 199
 - PSI, 199
 - VSI, 200
- Non-Gaussian probability distribution
 - manufacturing functions, 408
- Non-worst-case tolerance analysis techniques
 - Monte Carlo analysis method
 - device parameters, 382
 - “drop-in” test, 385
 - MEMS manufacturing process, 382, 383
 - probability distribution function, 383–386
 - pseudorandom number generator, 383
 - non-sampling, parameter value, 381

- O**
- Optical microscopy
 - accuracy of measurements, 177
 - calibration, 177
 - compound, 175
 - considerations, 174
 - dark-field, 176
 - DIC/Nomarski, 176
 - dimensional measurements, 177
 - lens elements, 174
 - magnification, 174
 - MEMS manufacturing, 174
 - resolution, 174
 - reticule, 177
 - transmission field mode, 176
 - transmitted light, 176
- Optimizing manufacturing cost function, 505, 506

- P**
- Packaging, 276
- Parameter variation reduction, 468
 - design centering, 473
 - flow resistance, 475
 - function mean, 474
 - manufacturing cost, 475
 - Monte Carlos analysis, 474
 - standard deviations, 474

- yield analysis, 474
- Parameter variations, 310
- Parametric testing, 305, 306
- Parametric yield
 - acceptance function, 401, 402
 - acceptance range, 401, 403–405
 - example
 - acceptance range, 409, 410
 - microchannel device, 408, 409
 - manufacturing function, 402–404
 - Monte Carlo analysis, 400
 - parameter space, 405–407
 - performance space, 406
 - probability distribution function, 401
 - quality control, 404, 420
- Parametric yield testing, 393
- Particle measurements, 197, 198
- Pascal distribution, 343
- Peltier effect, 20
- Phase-shifting interferometry (PSI), 199
- Phosphosilicate glass (PSG), 54, 284
- Photoconduction effect, 19, 20
- Photodetector, 188
- Photolithography
 - cross section, 77
 - deep-UV, 77
 - design rules, 80
 - forms, 76
 - g-line, 77
 - h-line, 77
 - i-line, 77
 - layer-to-layer registration alignment, 81
 - methods, 78
 - NA values, 79
 - negative resist, 77
 - optical radiation, 76, 77
 - optical wavelength radiation, 76
 - patterns, 76
 - photoresist layer, 76
 - photosensitive polymer, 76
 - positive resist, 77
 - pre-existing thin-film layer, 76
 - projection, 78
 - resolution, 80
 - SADP, 80
 - self-aligned process, 81
 - submicron precision, 79
 - tools, 79
 - wafer-track systems, 78
- Photolithography processing step, 45
- Physical vapor deposition (PVD), 107
 - advantages, 62
 - EBPVD, 63
 - evaporation
 - crystal sensor, 64
 - deposition rates, 64
 - EBPVD, 63
 - electron beam powers, 63
 - electron beam source, 64
 - high vacuum levels, 63
 - line-of-sight, 64
 - multicomponent thin films, 64
 - pre-existing topography, 64
 - thermal process, 62
 - thermionic emission, 63
- Piezoelectric materials, 114
- Piezoelectric transducers, 24–26
- Piezoelectricity, 15, 16
- Piezoresistive material, 12, 13
- Planar dimension variations, 458
- Planar location offsets, 458
- Plasma enhanced atomic layer deposition (PEALD), 61
- Plasma-enhanced chemical vapor deposition (PECVD), 33, 54
 - cold-walled parallel plate, 59
 - doping gases, 58
 - free ions, 58
 - hot-walled parallel plate, 59
 - lower temperatures, 58
 - plasma, 58
- Platinum, 107
- Poisson distribution, 344
- Poly(methyl methacrylate) (PMMA), 124
- Polydimethylsiloxane (PDMS), 112
- Polyimide, 112, 113
- Polymers
 - ceramics, 113
 - PDMS, 112
 - polyimide, 112, 113
 - SU-8, 111
- Polymethylmethacrylate (PMMA), 125
- PolyMUMPS™ process technology, 310
 - ANCHOR1 mask pattern, 284
 - device types, 289
 - HF, 289
 - LPCVD, 284
 - LPCVD polysilicon, 290, 291
 - oxide1 layer, 284
 - parameter variations, 298, 299
 - layer thickness, 299
 - line widths, 299
 - material layers, 298
 - material property values, 301
 - residual stresses and electrical resistances, 300

- PolyMUMPS™ process technology (*cont.*)
 photolithography, 284
 POLY1_POLY2_VIA level, 286
 Poly2 layer, 288
 process sequence, 284, 285
 prototyping program, 284
 PSG, 284
- Pre-deposition, 69
- Probability distribution function, 329, 336
 401, 411
- Process agnostics, 279
- Process integration, 275
 concept phase, 279
 design models, 282
 development team, 279
 DOE, 280
 lateral dimensions, 281
 MEMS microsystems, 275
 MEMS polysilicon cantilever, 276
 pioneer/scout wafer, 281
 process runcard/process traveler, 278
 short-loop process, 280
 strategy/set of principles, 279, 280
 test structures, 280
 testing and packaging, 276
 vertical dimensions, 281
 yield degradation, 282
- Process modules, 31
- Process sequences, 31, 275
- Process technology
 definition, 32
- Processing steps, 31
 definition, 30
- Pseudorandom number generator, 383
- Q**
- Quartz, 141
- R**
- Radio-frequency (RF), 60, 66
- Raman spectroscopy, 216
- Random parameter variations
 chi-squared testing, 338–341
 distribution curve, 331, 332
 micro-beam, 325–327
 normal distribution, 335, 336
 probability distribution curve, 327
 probability distribution function, 329, 330
 standard deviation, 330
 statistical parameters, 330
 t-statistic distribution, 337, 338
- Random variations, 317, 387
- Rapid thermal anneal (RTA), 254
 configuration, 82
 ion implantation, 82
 silicides, 83
 technique attractive, 83
- Rational subgroups, 439
- Reactive ion etch (RIE), 86, 88, 108, 116
 143, 325
- Reep, reactive ion etching (DRIE), 356
- Regionalization, 411
- Resistance-capacitance (RC), 84
- Resistive sensing elements, 11
- Resistor, 10, 11
- Reticule/ocular scale, 177
- Rutherford backscattering spectroscopy (RBS), 215
- S**
- Sacrificial layer, 277
- Scanning electron microscope (SEM), 180
 calibration procedures, 182
 detector signal, 181
 development tool, 181
 dimensional measurement, 181, 182
 emitter device, 183
 magnification, 181
 types, 181
 x-rays, 182
- Scanning electron microscope (SEM) image,
 142, 154
- Scanning transmission electron microscopy (STEM), 213
- Scanning tunneling microscope (STM)
 atomic-level resolution, 207
 calibration standards, 207
 closed-loop feedback circuit, 207
 conductive metal material, 206
 gold material layer, 207, 208
 piezoelectric/electrostatic actuation, 206
 repeatability, 207
 stylus profilometer, 206
 tunneling tip, 206
 ultrahigh vacuum conditions, 207
- Scanning tunneling microscope (STM), 17
- Scanning white light interferometry (SWLI), 199
- Secondary ion mass spectrometry (SIMS), 205,
 213, 221
- Seebeck effect, 20, 21
- Self-aligned double patterning (SADP)
 method, 80

- Semiconductor, 38
 - attribute, 42
 - band gap diagram, 42
 - charge carriers, 43
 - periodic table, 43
- Semiconductor-based manufacturing technologies, 1
- Sensitivity analysis
 - differential sensitivity, 499
 - generalized methods, 501–504
 - Monte Carlo analysis, 498
 - performance function, 500, 501
 - performance/manufacturing function, 499, 500
 - Taylor's series, 499, 500
- Shape-memory alloys (SMAs), 27, 28, 116, 117
- Silicon
 - crystal plane, 42
 - crystallographic orientation, 39, 41
 - diamond cubic crystal lattice structure, 38
 - EGS, 39
 - germanium, 38
 - material properties, 40
 - MEMS manufacturing, 38
 - semiconductor, 42
 - semiconductor material, 38
 - tetravalent metalloid, 38
 - wafers, 39
- Silicon (Si)
 - capacitive-based sensors, 102
 - dopant gases, 103
 - epitaxial process, 103
 - LPCVD, 102
 - MEMS device, 102
 - micromachining process sequences, 101
 - polysilicon depositions, 102
 - PVD techniques, 103
 - surface micromachining processes, 102
- Silicon carbide (SiC), 39, 104, 105, 143, 144
- Silicon Dioxide (SiO₂), 110
- Silicon dioxide materials, 141
- Silicon nitride (SiN), 54, 109, 110
- Silicon nitride layer, 291
- Silicon–germanium (SiGe), 39, 103, 104
- Silicon-on-insulator (SOI), 100
- Simplicial approximation, 414
- Simulation, 453
- Single-crystal silicon, 54
- Specialized metrology method
 - AFM, 208–210
 - EDXS, 210, 212
 - equipment and methods, 222
 - FIB, 203–205
 - STM, 206–207
- Spin-on glasses (SOG), 84
- Spreading sheet resistance measurements
 - carrier concentration, 220
 - doping concentrations, 221
 - effective electrical contact, 219
 - electrical resistivity, 221
 - microsystems manufacturing, 218
 - semiconductor substrate, 218, 219
 - silicon wafer, 220
 - SIMS, 221
- Sputter physical vapor deposition, 266, 267
- Sputtering
 - DC bias, 66
 - disadvantages, 67
 - matching network, 66
 - multiple component alloys, 67
 - plasma, 65
 - residual gases, 65
 - RF bias, 66
 - scattering, 65
 - S-gun magnetron, 66
 - target material, 65
 - types, 67
 - variation, 66
 - yields, 65
- Stage micrometer scale, 177
- Statistical process control (SPC), 7, 228
 - acceptance rang, 421
 - attributes, control charts
 - c-chart, 432, 433
 - conforming/non-conforming, 430, 431
 - control limits, 432, 434
 - manufacturing process, 431
 - non-conforming units, 433
 - control chart
 - microsystems manufacturing, 424
 - non-random patterns, identification, 434, 435
 - quality control, 424
 - control chart, variable
 - characteristic, 424
 - LCL, 425
 - R-chart, 426, 427
 - standard deviation, 425, 428, 429
 - UCL, 426
 - defining, 420
 - manufacturing process, 421
 - process capability
 - acceptance range, 435–437, 445
 - manufacturing function, 435, 436
 - ratio, 437–439
 - specification limits, 435, 438

Statistical process control (SPC) (*cont.*)

- rational subgroups
 - critical dimension measurement, 443, 444
- LPCVD deposition, 442, 443
- non-random event, 439
- quality control, 439, 443–445
- spatial variations, 440
- substrate variations, 440–442

Steady-state conditions, 49

Stereomicroscopy, 179, 180

Stress measurement

- anisotropic, 196
- biaxial forces, 195
- elastic properties, 195
- nondestructive routine measurement, 195
- polysilicon, 195
- residual stress levels, 193, 194
- single-crystal silicon substrate, 196
- Stoney equation, 196
- substrate curvature, 195, 196
- thin-film layers, 193
- tool, 196

Structural layer, 277

Stylus profilometer

- calibration standards, 190
- functional aspect, 189, 190
- photolithography, 189
- resolution, 189
- scan lengths, 191
- thin-film layer's thickness, 189

Substrate curvature method, 196

Substrate manufacturing yield, 391

Surface micromachining, 144–147

Systematic (bias) variations, 387

T

Tapping mode imaging, 209

Technology CAD (TCAD), 452

Test structures

- nano-indentation, 242
- stress gradients, 241, 242
- stress states, 240
- thin-film residual stress, 237–240
- Young's modulus, 234–237

Testing, 276

Thermal diffusion, 68–71

Thermal effects, 26, 27

Thermal sensing capability, 11

Thermal SiO₂, 250–252

Thermoelectric effect, 20–22

Thin-film deposition technologies

thermal oxidation

- crystallographic orientation, 50
- Deal and Grove model, 49
- Fick's laws, 49
- MOS transistors, 48
- oxidation system, 51, 52
- oxidizing agent, 48
- rate constants, 50, 51
- silicon, 49
- silicon dioxide (SiO₂), 47, 48
- steady-state conditions, 49

Thin-film material properties

evaporative physical vapor deposition, 263, 265

LPCVD polysilicon

- crystal orientation, 252
- electrical properties, 253
- electrical resistivity, 252
- in situ doping, 252
- MEMS devices, 251
- nitrogen, 254
- polycrystalline microstructure, 252
- post-deposition anneals, 254
- processing conditions, 251
- residual stress, 252, 254–256
- PECVD polycrystalline silicon, 263, 264
- PECVD silicon dioxide (SiO₂), 259, 261
- PECVD silicon nitride (SiN), 261, 262
- thermal SiO₂, 250–252

Thin-film semiconductors

- diamond, 105, 106
- dielectrics, 109
 - SiN, 109, 110
 - SiO₂, 110
- Ge, 104
- magnetic materials, 117, 118
- metal oxides, 108
- metals, 106–108
- piezoelectric materials, 114
- polymers (*see* Polymers)
- Si, 101–103
- SiC, 104, 105
- SiGe, 103, 104
- SMAs, 116–117

Tolerance interval, 367

Total thickness variation (TTV), 100

Transducers, 3

Transmission electron microscopy (TEM), 212

Transmitted light microscopy, 176

Transparent substrates, photolithography, 128

Tunneling effect, 16, 17

Twyman–Green interferometry, 199

U

- Ultra-nanocrystalline diamond (UNCD), 106
- Ultrasonic wafer bonding inspection system, 203
- Upper control limit (UCL), 425

V

- Validation, 453
- van der Pauw structure, 245
- Vapor hydrofluoric (HF) acid, 138
- Variation design, 448
- Verification, 453
- Vertical dimension variations, 458
- Vertical scanning interferometry (VSI), 200

W

- Wafer bonding, 100, 147–150
- Wafer bonding inspection
 - CMOS imaging camera, 202
 - defects, 201
 - infrared inspection system, 201
 - infrared radiation, 202
 - Newton rings, 202
 - quality, 201
 - semiconductor material, 201
 - wafer surfaces, 200
- Wafer curvature measurements, 237
- Wafer-track systems, 78
- Wet etches, 107
- Worst-case variation analysis
 - device output functions, 379, 380
 - elements, 377–379
 - macroscale manufacturing, 377
 - MEMS devices, 381
 - Monotonicity, 381
 - parameter values, 377

X

- Xenon difluoride (XeF₂), 137, 138
- X-ray diffraction, 213
- X-ray fluorescence (XRF), 214, 215
- X-ray lithography, 124
- X-ray photoelectron spectroscopy (XPS), 214
- X-ray radiation, 124

Y

- Yield estimations
 - Monte Carlo analysis
 - advantage, 418
 - central limit theorem, 419
 - probability distribution function, 418–420
 - regionalization
 - computational cost, 413
 - defining, 411
 - device output, 412
 - probability distribution function, 411
 - simplicial approximation, 414–418
- Yield monitoring and analysis methods
 - types
 - functional yield testing, 393
 - parameter yield testing, 393
- Yield testing, 393
- Young's Modulus
 - test structure, 234
 - drive voltage signal, 235, 236
 - material layer, 234
 - micromachined, 235
 - resonant frequency, 236

Z

- Zinc oxide (ZnO), 15, 114